



30V Dual N-Channel Enhancement Mode MOSFET

Voltage 30 V Current 6 A

Features

- RDS(ON), VGS@10V, ID@6A< $35m\Omega$
- RDS(ON), VGS@4.5V, ID@4A<40mΩ
- RDS(ON), VGS@2.5V, ID@2A<54mΩ
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- High density cell design for ultra low on-resistance
- Green molding compound as per IEC61249 Std. (Halogen Free)

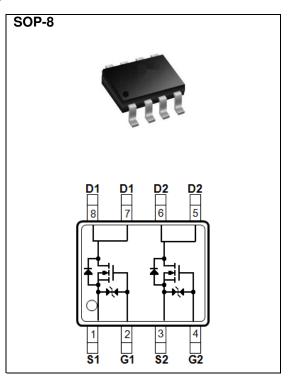
Mechanical Data

• Case: SOP-8 package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0029 ounces, 0.083 grams

Marking: L9812



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 12	V	
Continuous Drain Current	T _A =25°C		6		
	T _A =70°C	l _D	4.8	Α	
Pulsed Drain Current (Note 1)		I _{DM}	24	Α	
Power Dissipation	T _A =25°C	P _D	2	W	
	T _A =70°C		1.3		
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance					
- Junction to Ambient, t≤10s (Note 5)		$R_{\theta JA}$	62.5	°C/W	





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.8	1.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =6.0A	-	30	35	mΩ
		V _{GS} =4.5V,I _D =4.0A	-	33	40	
		V _{GS} =2.5V,I _D =2.0A	-	41	54	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 12V,V _{DS} =0V	-	-	<u>+</u> 10	uA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V_{DS} =15V, I_{D} =6.0A, V_{GS} =4.5V (Note 1,2)	-	5.1	-	nC
Gate-Source Charge	Q_gs		-	0.8	-	
Gate-Drain Charge	Q_{gd}		-	1.4	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	421	-	pF
Output Capacitance	Coss		-	43	-	
Reverse Transfer Capacitance	Crss	f=200KHZ	-	35	-	
Turn-On Delay Time	td _(on)	\/ 45\/ 404	-	3.3	-	ns
Turn-On Rise Time	tr	V_{DD} =15V, I_{D} =1.0A, V_{GS} =10V, R_{G} =3 Ω (Note 1,2)	-	24	-	
Turn-Off Delay Time	td _(off)		-	19	-	
Turn-Off Fall Time	tf	n _G =312	-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	1		-	-	6	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =6.0A, V _{GS} =0V	-	0.86	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

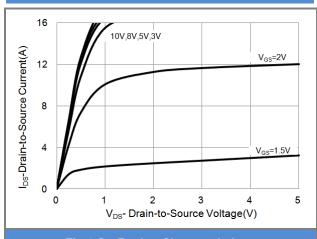


Fig.1 On-Region Characteristics

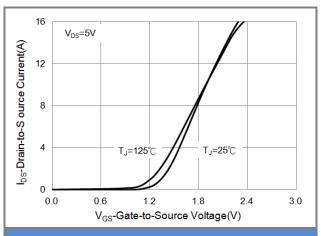


Fig.2 Transfer Characteristics

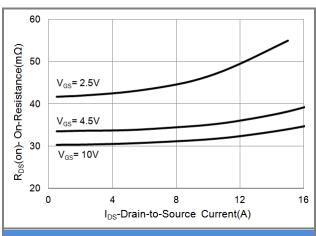


Fig.3 On-Resistance vs. Drain Current

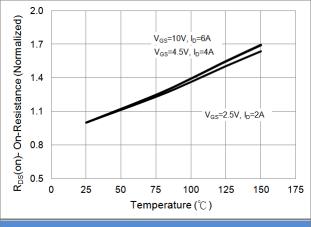


Fig.4 On-Resistance vs. Junction temperature

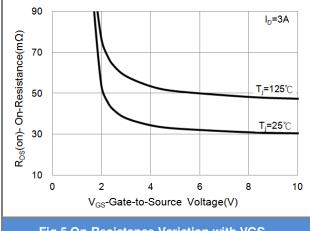


Fig.5 On-Resistance Variation with VGS.

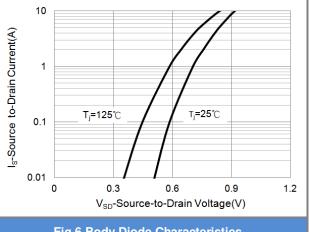


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

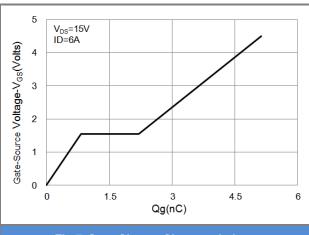


Fig.7 Gate-Charge Characteristics

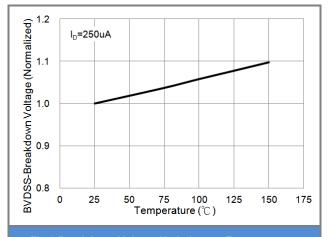


Fig.8 Breakdown Voltage Variation vs. Temperature

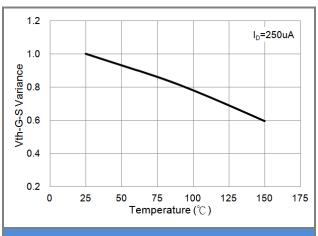


Fig.9 Threshold Voltage Variation with Temperature.

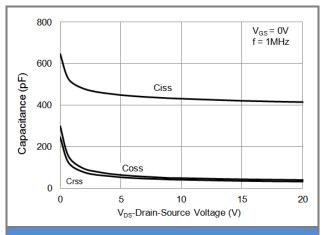


Fig.10 Capacitance vs. Drain-Source Voltage.

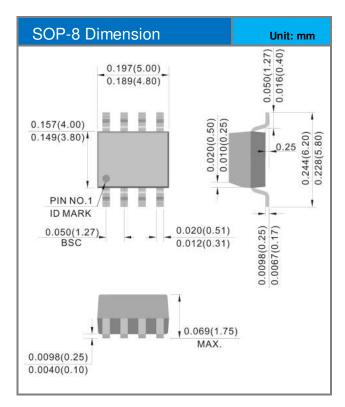


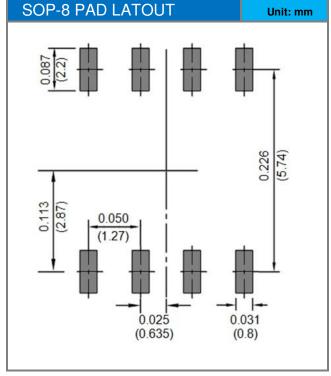


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJL9812_R2_00001	SOP-8	2.5K pcs / 13" reel	L9812	Halogen free

Packaging Information & Mounting Pad Layout









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